AMENDMENTS TO THE CLAIMS

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-6. (cancelled)

7. (original): A method of making a semiconductor device comprising:

depositing a layer of oxide proximate a first surface of a semiconductor substrate;

forming a gate oxide layer on the first surface, adjacent to the deposited oxide layer;

forming a pair of active areas in the first surface, adjacent the deposited oxide layer and gate oxide layer;

forming a gate electrode by depositing a conductive layer over the gate oxide layer;

depositing a dielectric layer over the gate electrode, active areas, and deposited oxide layer; and

forming electrical contacts to the pair of active areas and the gate electrode.

8. (original): The method of Claim 7, further comprising thermally growing a thermal oxide layer before depositing the layer of oxide on the first surface of the semiconductor substrate.

9. (original): The method of Claim 7, wherein the semiconductor substrate is P type silicon.

10. (original): The method of Claim 7, wherein the active areas are formed by impurity implant and diffusion.

11. (original): The method of Claim 7, wherein the active areas are n doped regions.

12. (original): The method of Claim 7, wherein the conductive layer over the gate oxide layer is polysilicon.

13. (original): The method of Claim 7, wherein the dielectric layer is silicon dioxide.

Claims 14-18 (cancelled)

19. (currently amended): A method comprising ~~of~~ manufacturing a fluid ejection device~~, the method comprising~~ by:

depositing a current prevention layer proximate a first surface of a semiconductor substrate; ~~and~~

forming first and second field effect transistors (FETs), wherein each said FET includes a gate electrode with associated active areas formed in the first surface of the semiconductor substrate having the deposited current prevention layer, wherein the current prevention layer includes a region that minimizes

current flow between the active areas of the first FET with respect to the active areas of the second FET; and

forming a firing chamber above the current prevention layer.

20. (original): The method of Claim 19, wherein the current prevention layer is a dielectric.

21. (original): The method of Claim 19, wherein the current prevention layer is an oxide.

22. (currently amended): A method comprising:

depositing a layer of oxide proximate a first surface of a semiconductor substrate;

exposing a portion of the first surface of the semiconductor substrate; and

forming a field effect transistor (FET) on the exposed portion of the first surface of the substrate having the deposited oxide layer, wherein the FET includes a gate electrode with associated active areas formed after the exposing in the first surface of the semiconductor substrate.

23. (previously presented): A product formed by the method of Claim 22.

24. (previously presented): A method of making a semiconductor device comprising:

depositing a layer of oxide proximate a first surface of a semiconductor substrate;

exposing a portion of the first surface of the semiconductor substrate;

forming a gate oxide layer on the exposed portion of the first surface, adjacent to the deposited oxide layer;

forming a pair of active areas in the exposed portion of the first surface, adjacent the deposited oxide layer and gate oxide layer;

forming a gate electrode by depositing a conductive layer over the gate oxide layer;

depositing a dielectric layer over the gate electrode, active areas, and deposited oxide layer; and

forming electrical contacts to the pair of active areas and the gate electrode.

25. (previously presented): The method of Claim 24, further comprising thermally growing a thermal oxide layer before depositing the layer of oxide on the first surface of the semiconductor substrate.

26. (previously presented): The method of Claim 24, wherein the semiconductor substrate is P type silicon.

27. (previously presented): The method of Claim 24, wherein the active areas are formed by impurity implant and diffusion.

28. (previously presented): The method of Claim 24, wherein the active areas are n doped regions.

29. (previously presented): The method of Claim 24, wherein the conductive layer over the gate oxide layer is polysilicon.

30. (previously presented): The method of Claim 24, wherein the dielectric layer is silicon dioxide.

31. (previously presented): A semiconductor device produced by the method of claim 24.

32. (previously presented): A semiconductor device produced by the method of claim 7.

33. (previously presented): A fluid ejection device produced by the method of claim 19.